MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J327R

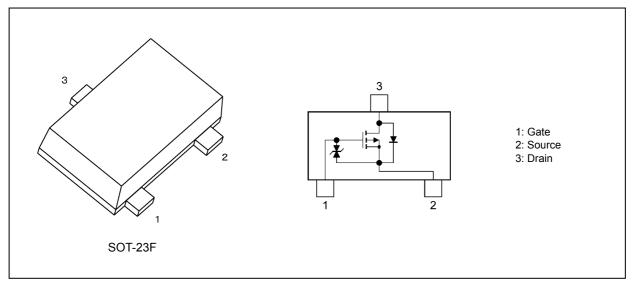
### 1. Applications

Power Management Switches

### 2. Features

- (1) 1.5-V drive
- (2) Low drain-source on-resistance
  - $\begin{array}{l} : \mathrm{R}_{\mathrm{DS(ON)}} = 240 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -1.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 168 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -1.8 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 123 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -2.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 93 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -4.5 \ \mathrm{V}) \end{array}$

### 3. Packaging and Internal Circuit



Rev.1.0

### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				V <sub>DSS</sub>	-20	V
Gate-source voltage				V <sub>GSS</sub>	±8	V
Drain current (DC)			(Note 1)	Ι <sub>D</sub>	-3.9	А
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	-7.8	
Power dissipation			(Note 3)	PD	1	W
Power dissipation		t = 10 s	(Note 3)		2	
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C
- Note 2: Pulse width (PW)  ${\leq}10$  ms, duty  ${\leq}~1\%$
- Note 3: Device mounted on a FR4 board.
  - (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad : 645 mm²)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±8 V		_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_	_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 5 V	-15	_	—	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1 mA	-0.3	_	-1.0	1
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -1.5 A, V <sub>GS</sub> = -4.5 V	_	78.5	93	mΩ
			I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -2.5 V	_	97.5	123	
			I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.8 V		120	168	
			I <sub>D</sub> = -0.25 A, V <sub>GS</sub> = -1.5 V	—	141	240	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1.0 A	2.8	5.6	_	s

Note 1: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 3: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	—	290	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	32	—	
Output capacitance	C <sub>oss</sub>		_	44	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = -10 V, I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = 0 to -2.5 V, R <sub>G</sub> = 4.7 $\Omega$		12.0		ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, Input: t <sub>r</sub> , t <sub>f</sub> < 5 ns Common source	_	46.2		

### 5.3. Switching Time Test Circuit

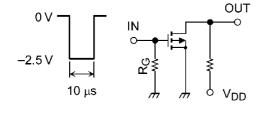


Fig. 5.3.1 Switching Time Test Circuit

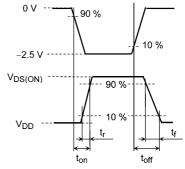


Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -10 V, I <sub>DS</sub> = -3.9 A,	_	4.6	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = -4.5 V	_	3.4	_	
Gate-drain charge	Q <sub>gd</sub>		_	1.2	—	

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

### 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{\text{DSF}}$	$I_{\rm D}$ = 3.9 A, $V_{\rm GS}$ = 0 V	_	0.97	1.2	V

Note 1: Pulse measurement.

### 6. Marking

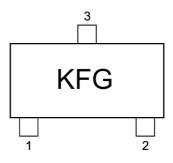
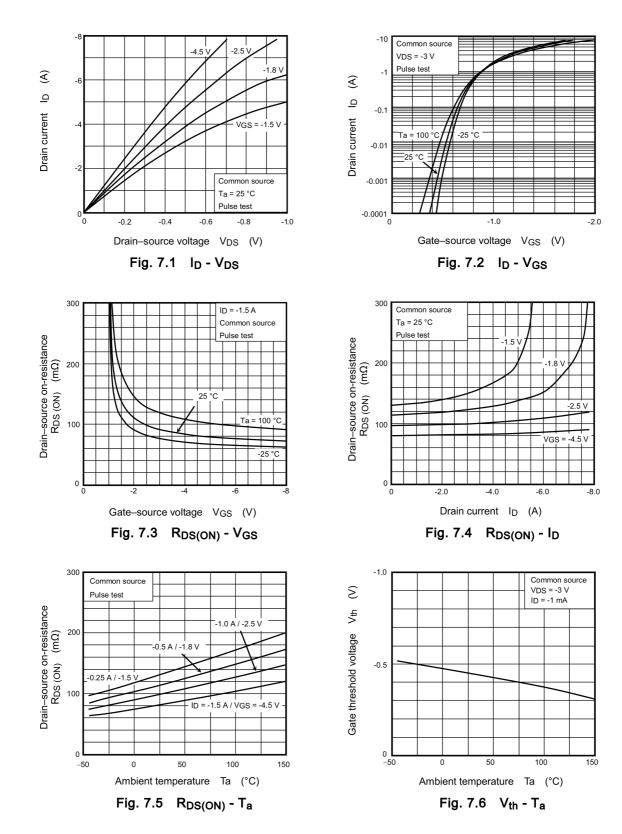


Fig. 6.1 Marking

### 7. Characteristics Curves (Note)



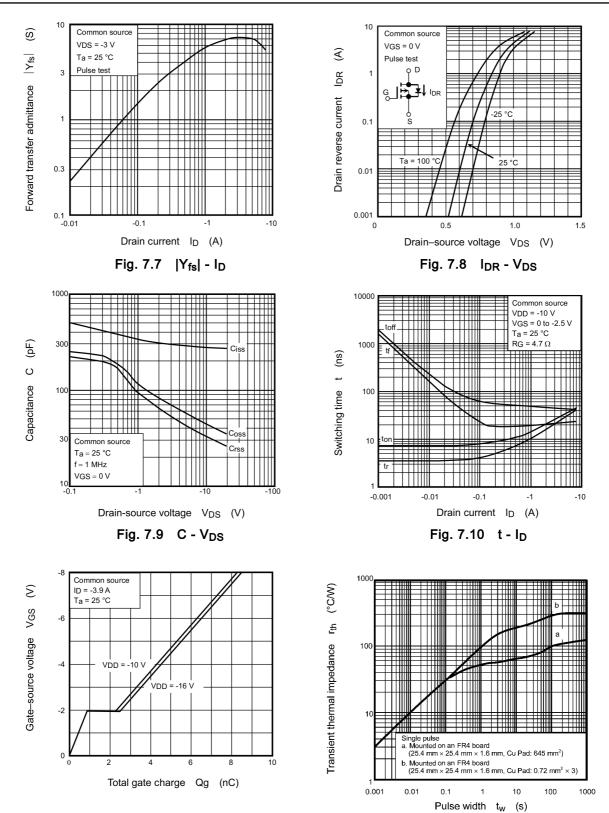
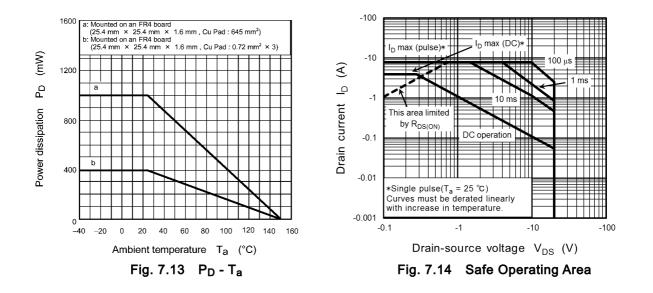


Fig. 7.11 Dynamic Input Characteristics

Fig. 7.12 r<sub>th</sub> - t<sub>w</sub>





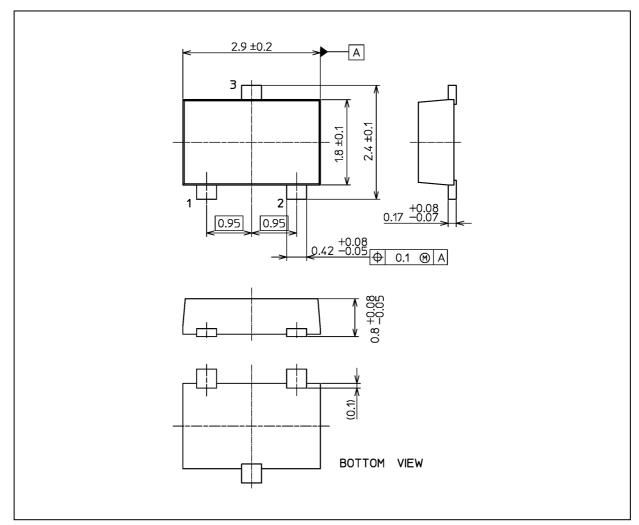
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM3J327R

### Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
Nickname: SOT-23F	

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